

## 阅读申明

- 1.本站收集的数据手册和产品资料都来自互联网，版权归原作者所有。如读者和版权方有任何异议请及时告之，我们将妥善解决。
- 2.本站提供的中文数据手册是英文数据手册的中文翻译，其目的是协助用户阅读，该译文无法自动跟随原稿更新，同时也可能存在翻译上的不当。建议读者以英文原稿为参考以便获得更精准的信息。
- 3.本站提供的产品资料，来自厂商的技术支持或者使用者的心得体会等，其内容可能存在描述上的差异，建议读者做出适当判断。
- 4.如需与我们联系，请发邮件到marketing@iczoom.com，主题请标有“数据手册”字样。

## Read Statement

1. The datasheets and other product information on the site are all from network reference or other public materials, and the copyright belongs to the original author and original published source. If readers and copyright owners have any objections, please contact us and we will deal with it in a timely manner.
2. The Chinese datasheets provided on the website is a Chinese translation of the English datasheets. Its purpose is for reader's learning exchange only and do not involve commercial purposes. The translation cannot be automatically updated with the original manuscript, and there may also be improper translations. Readers are advised to use the English manuscript as a reference for more accurate information.
3. All product information provided on the website refer to solutions from manufacturers' technical support or users the contents may have differences in description, and readers are advised to take the original article as the standard.
4. If you have any questions, please contact us at marketing@iczoom.com and mark the subject with "Datasheets" .

## HIGH EFFICIENCY ULTRAFAST DIODE

### MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	Up to 2 x 10A
$V_{RRM}$	200 V
$T_j$ (max)	175 °C
$V_F$ (typ)	0.78 V
$t_{rr}$ (typ)	21 ns

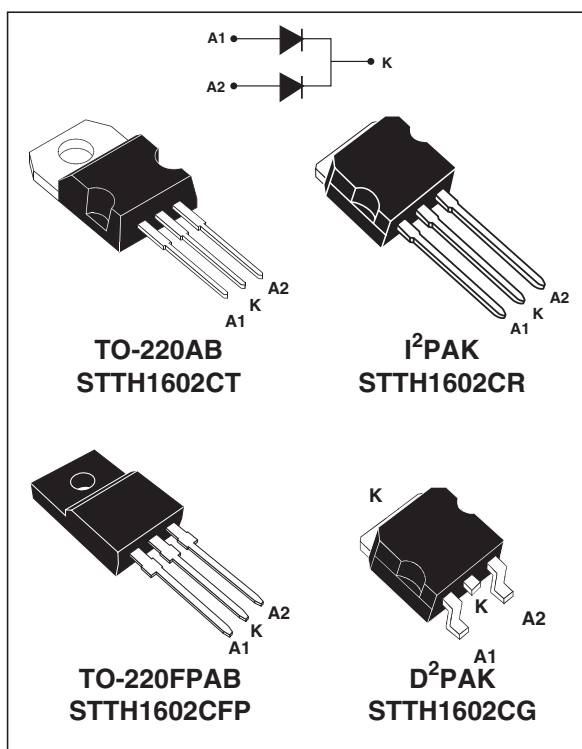
### FEATURES AND BENEFITS

- Suited for SMPS
- Low losses
- Low forward and reverse recovery times
- Low leakage current
- High junction temperature
- Insulated package: TO-220FPAB

### DESCRIPTION

Dual center tap rectifier suited for Switch Mode Power Supplies and High frequency DC to DC converters.

Packaged in TO-220AB, D<sup>2</sup>PAK, TO-220FPAB and I<sup>2</sup>PAK, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage		200	V	
$I_{F(RMS)}$	RMS forward current		30	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	TO-220AB / I <sup>2</sup> PAK / D <sup>2</sup> PAK	T <sub>c</sub> = 150°C Per diode	8	A
			T <sub>c</sub> = 140°C Per device	16	
			T <sub>c</sub> = 140°C Per diode	10	
			T <sub>c</sub> = 130°C Per device	20	
		TO-220FPAB	T <sub>c</sub> = 130°C Per diode	8	
			T <sub>c</sub> = 100°C Per device	16	
			T <sub>c</sub> = 110°C Per diode	10	
			T <sub>c</sub> = 75°C Per device	20	
$I_{FSM}$	Surge non repetitive forward current	tp = 10 ms Sinusoidal	80	A	
$T_{stg}$	Storage temperature range		- 65 + 175	°C	
$T_j$	Maximum operating junction temperature		175	°C	

## STTH1602C

### THERMAL PARAMETERS

Symbol	Parameter		Maximum	Unit	
$R_{th(j-c)}$	Junction to case	TO-220AB / I <sup>2</sup> PAK / D <sup>2</sup> PAK	Per diode	3.0	°C/W
			Per device	1.9	
		TO-220FPAB	Per diode	5.5	
			Per device	4.5	
$R_{th(j-c)}$	Coupling	TO-220AB / I <sup>2</sup> PAK / D <sup>2</sup> PAK	0.8	°C/W	
		TO-220FPAB	3.5		

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode1}) = P(\text{diode1}) \times R_{th(j-c)} (\text{per diode}) + P(\text{diode2}) \times R_{th(c)}$$

### STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	Tj = 25°C	$V_R = V_{RRM}$			6	μA
		Tj = 125°C			4	60	
$V_F^{**}$	Forward voltage drop	Tj = 25°C	$I_F = 8 \text{ A}$			1.1	V
		Tj = 25°C	$I_F = 16 \text{ A}$			1.25	
		Tj = 150°C	$I_F = 8 \text{ A}$		0.78	0.89	
		Tj = 150°C	$I_F = 16 \text{ A}$			1.05	

Pulse test: \* tp = 5ms, δ < 2%

\*\* tp = 380μs, δ < 2%

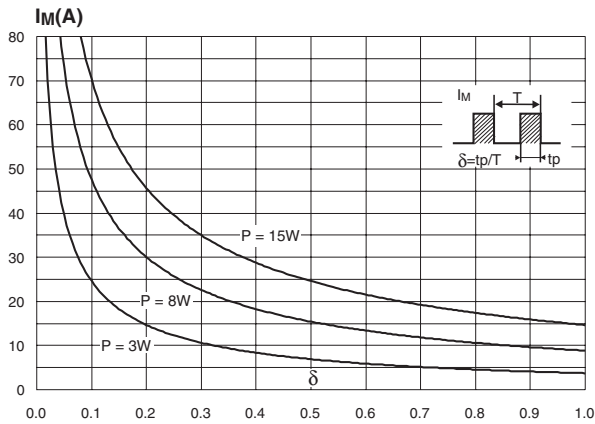
To evaluate the maximum conduction losses use the following equation :

$$P = 0.73 \times I_{F(AV)} + 0.020 I_{F(RMS)}^2$$

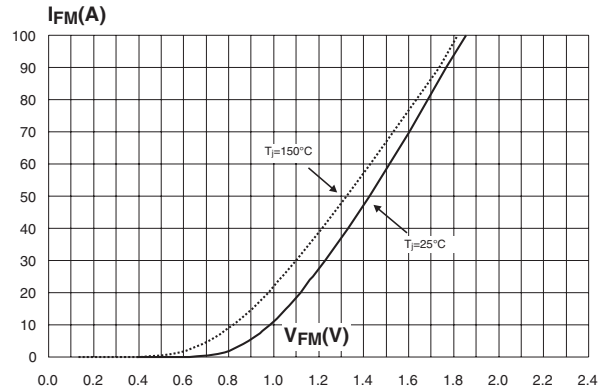
### DYNAMIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	Tj = 25°C	$I_F = 1 \text{ A}$ $V_R = 30\text{V}$ $di_F/dt = 100 \text{ A}/\mu\text{s}$		21	26	ns
$I_{RM}$	Reverse recovery current	Tj = 125°C	$I_F = 8 \text{ A}$ $V_R = 160\text{V}$ $di_F/dt = 200 \text{ A}/\mu\text{s}$		6.8	8.8	A
$t_{fr}$	Forward recovery time	Tj = 25°C	$I_F = 8 \text{ A}$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$			160	ns
$V_{FP}$	Forward recovery voltage	Tj = 25°C	$I_F = 8 \text{ A}$ $di_F/dt = 100 \text{ A}/\mu\text{s}$		2.4		V

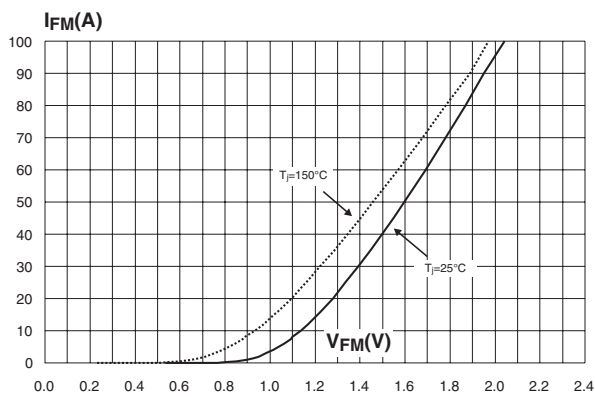
**Fig. 1:** Peak current versus duty cycle (per diode).



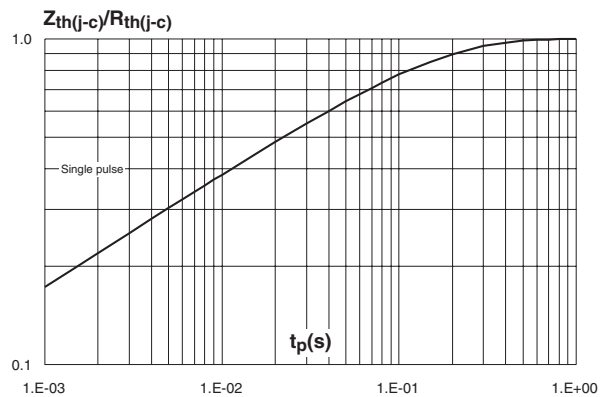
**Fig. 2-1:** Forward voltage drop versus forward current (typical values, per diode).



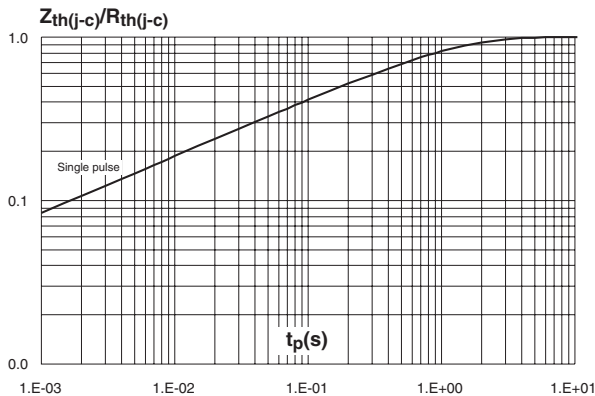
**Fig. 2-2:** Forward voltage drop versus forward current (maximum values, per diode).



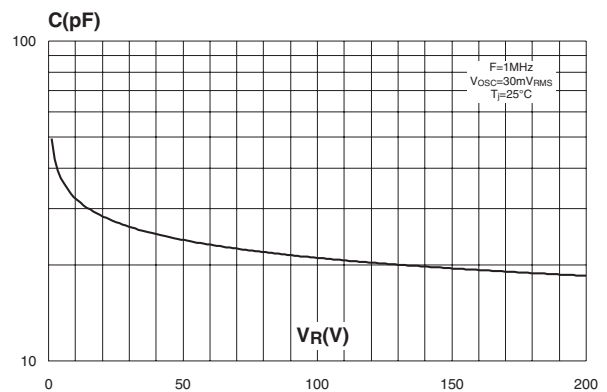
**Fig. 3-1:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220AB, D<sup>2</sup>PAK, I<sup>2</sup>PAK).



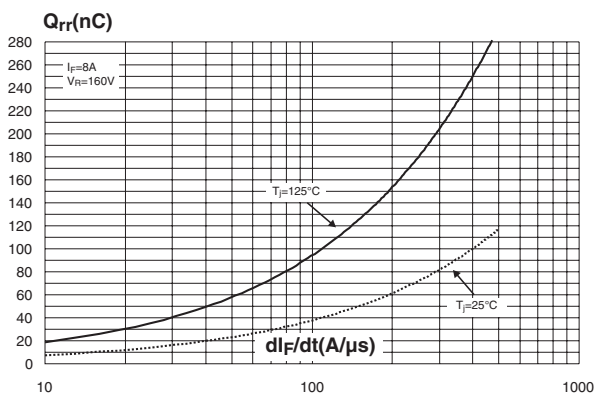
**Fig. 3-2:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAB).



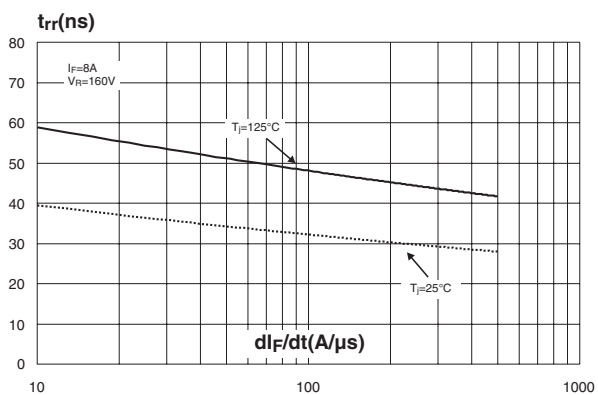
**Fig. 4:** Junction capacitance versus reverse voltage applied (typical values, per diode).



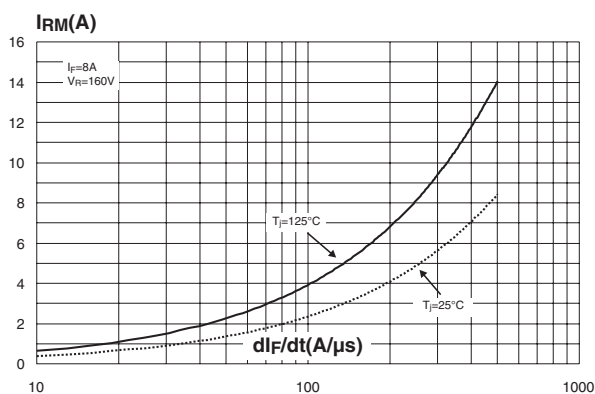
**Fig. 5:** Reverse recovery charges versus  $di_F/dt$  (typical values, per diode).



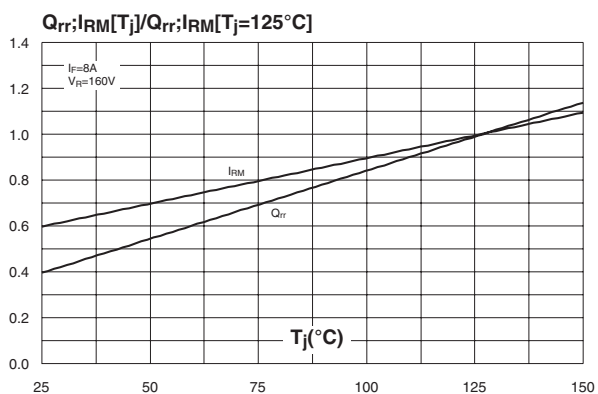
**Fig. 6:** Reverse recovery time versus  $di_F/dt$  (typical values, per diode).



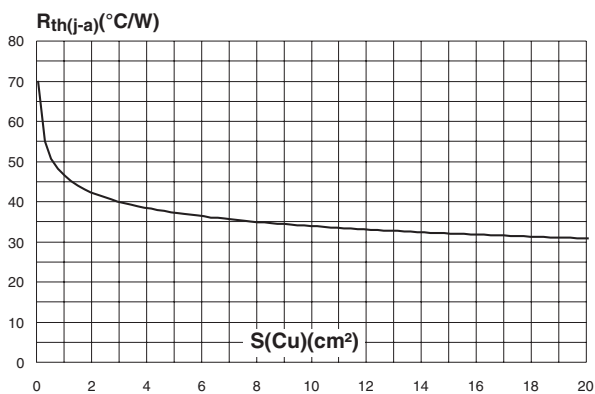
**Fig. 7:** Peak reverse recovery current versus  $di_F/dt$  (typical values, per diode).



**Fig. 8:** Dynamic parameters versus junction temperature.

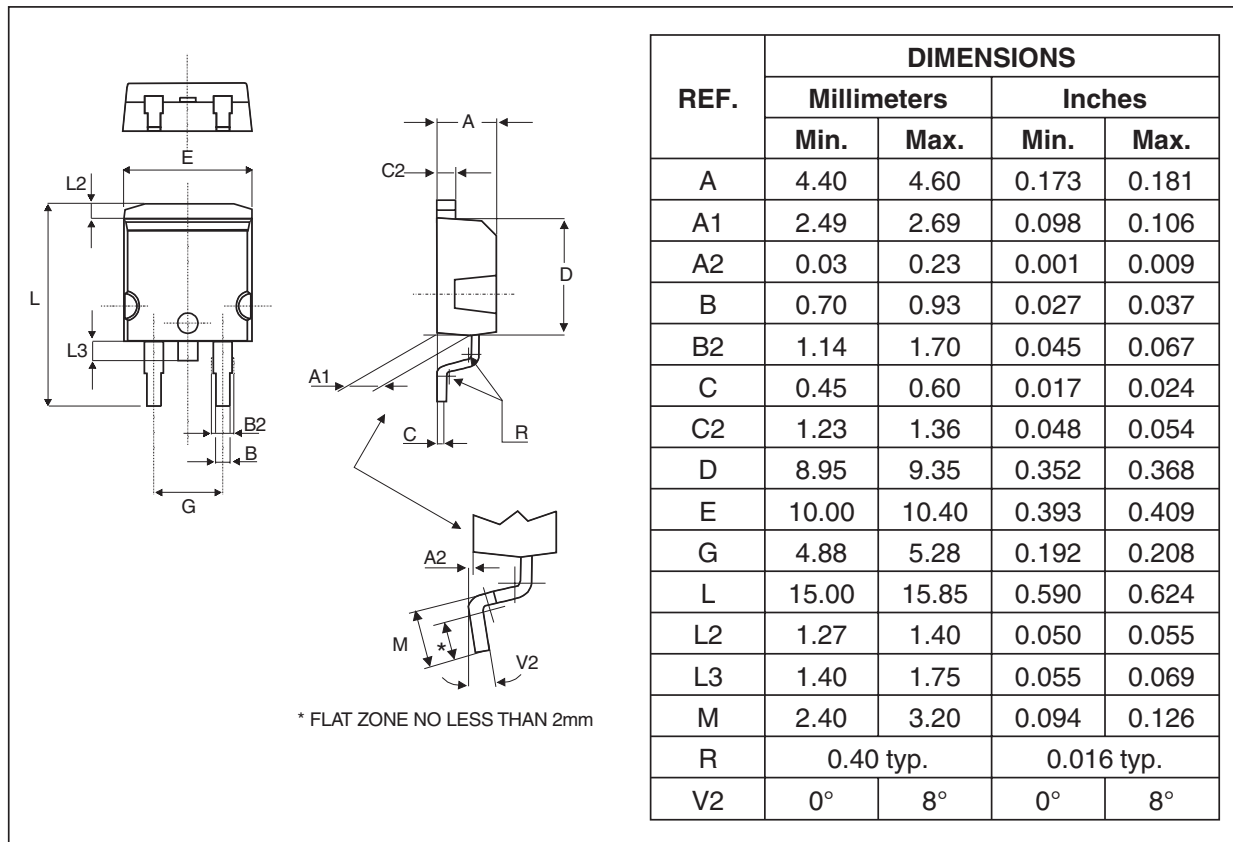


**Fig. 9:** Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4,  $\epsilon_{cu}$ : 35 $\mu$ m) for D<sup>2</sup>PAK.

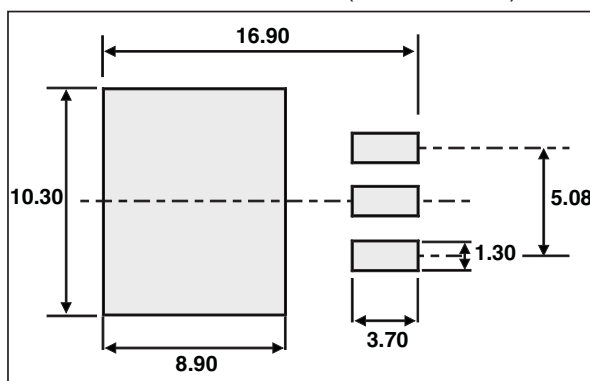


Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH1602CT	STTH1602CT	TO-220AB	2.23 g	50	Tube
STTH1602CG	STTH1602CG	D <sup>2</sup> PAK	1.48 g	50	Tube
STTH1602CG-TR	STTH1602CG	D <sup>2</sup> PAK	1.48 g	1000	Tape & reel
STTH1602CR	STTH1602CR	I <sup>2</sup> PAK	1.49 g	50	Tube
STTH1602CFP	STTH1602CFP	TO-220FPAB	1.70g	50	Tube

**PACKAGE MECHANICAL DATA**  
D<sup>2</sup>PAK

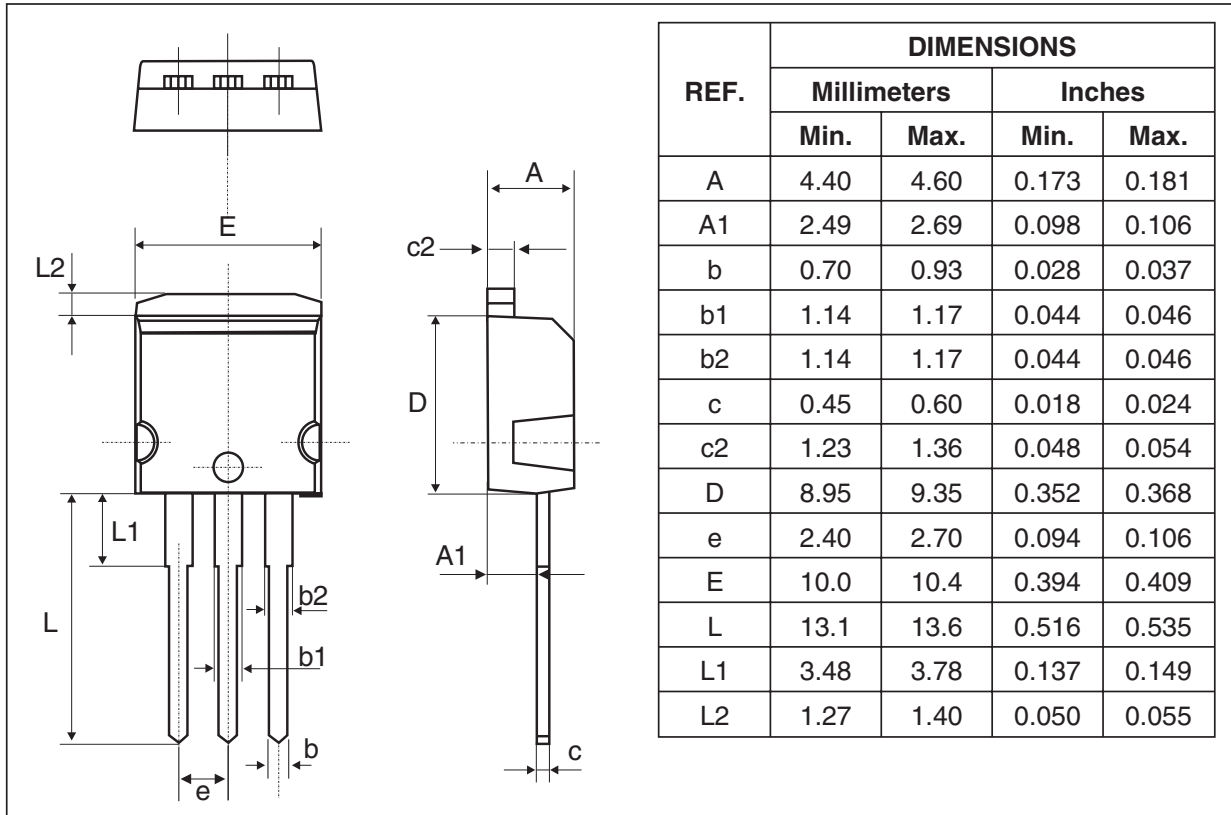


**FOOTPRINT DIMENSIONS** (in millimeters)

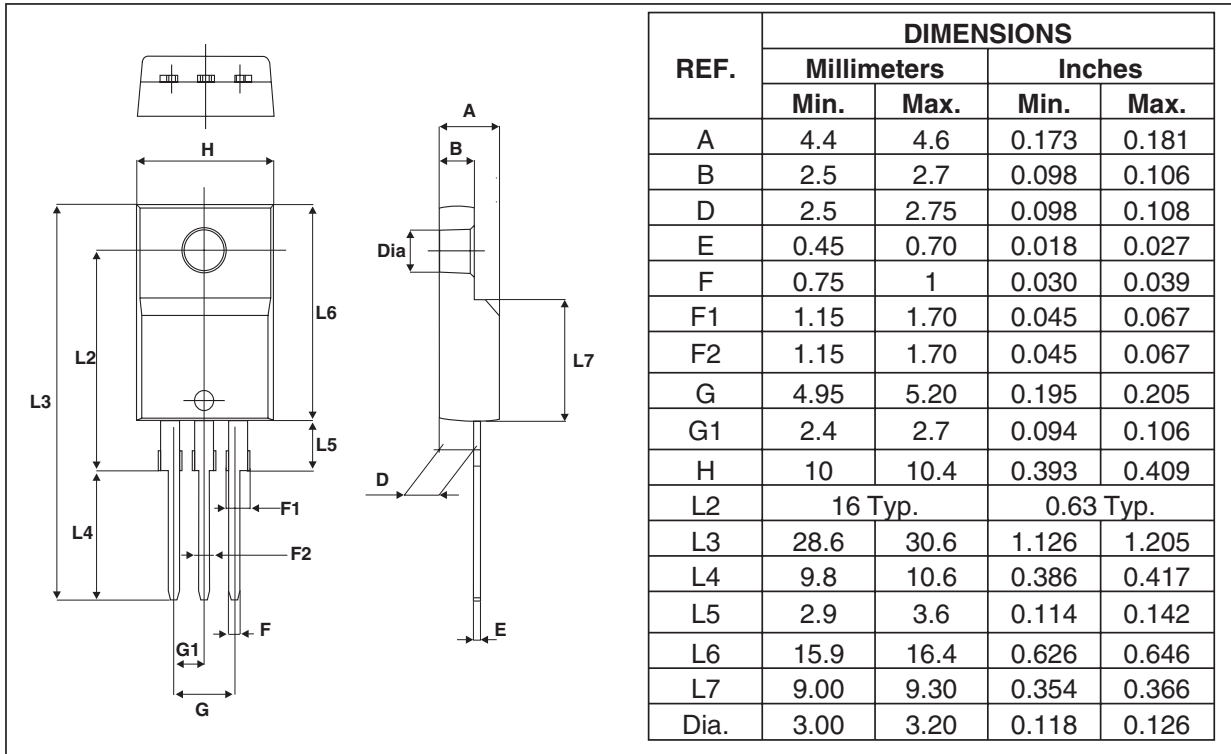


**STTH1602C**

**PACKAGE MECHANICAL DATA**  
I<sup>2</sup>PAK



**PACKAGE MECHANICAL DATA**  
TO-220FPAB



**PACKAGE MECHANICAL DATA**  
**TO-220AB**

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

- Epoxy meets UL94,V0
- Cooling method: by conduction (method C)
- Recommended torque value (TO-220AB): 0.8 N.m.
- Maximum torque value (TO-220AB): 1.0 N.m.
- Recommended torque value (TO-220FPAB): 0.55 N.m.
- Maximum torque value (TO-220FPAB): 0.7 N.m.

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.

All other names are the property of their respective owners.

© 2004 STMicroelectronics - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany -  
 Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain -  
 Sweden - Switzerland - United Kingdom - United States

[www.st.com](http://www.st.com)

